Attorney Docket No. 1217-032260

AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph beginning at page 11, line 20, with the following rewritten paragraph:

-- Fig. 1 is a schematic view showing an example of a single crystal pulling apparatus having the above structure. --

Please replace the paragraph beginning at page 18, line 5, with the following rewritten paragraph:

-- In most cases in which the coefficient of thermal conductivity in the direction of the thickness of the ceiling board 44 is smaller than 1000 W/m²·K, a heat radiation from the ceiling board 44 becomes insufficient so that a temperature gradient in the direction of the height of the single crystal pulling region 38 is not sufficient and a single crystal is not generated. Also in the case in which the growth of the single crystal is generated, moreover, a temperature distribution in the single crystal pulling region 38 becomes nonuniform so that internal strain and birefringence increase. On the other hand, in the case in which the coefficient of thermal conductivity in the direction of the thickness of the ceiling board 44 is greater than 50000 W/m²·K, the temperature gradient in the direction of the height is excessively increased, and it is difficult to stably growing grow a single crystal, resulting in the increase of birefringence. --

Please replace the paragraph beginning at page 23, line 8, with the following rewritten paragraph:

-- The partition wall 50 has such function that uniforming the function of keeping uniform the radiant heat from the melting heater 24 to heat the crucible 20. The lid member 52 has such function that the function of preventing the heat of the melting heater 24 from being let upward. In order to further reduce the strain of the single crystal, it is effective to further uniforming the maintain a uniform temperature

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around the liquid surface of the molten solution and to grow the single crystal around the liquid surface of the molten solution with gradually gradual cooling. The structure mentioned above is effective to realize these advantages. --

Please replace the paragraph beginning at page 29, line 16, with the following rewritten paragraph:

-- The crucible 20 made of high-purity graphite, which was set in the chamber 12, had an inner diameter of 38 cm (outer diameter: 40 cm) and a height of 30 cm. The heat-insulating wall 26 was a pitch type graphite molded heat insulator and had a coefficient of thermal conductivity of 9 W/m² K in the thickness direction. The ceiling board 44 was made of graphite and had a heat-radiating powder of 5000 W/m² K in the thickness direction. In the ceiling board, an observation hole to ensure view from [[a]] an inspection window 48 was formed in addition to an inserting hole 42 (diameter: 14 cm) for a single crystal pulling bar 32 shown in the figure, and the total opening area thereof was 13% of the upper end opening area of the surrounding heat-insulating wall 26. --